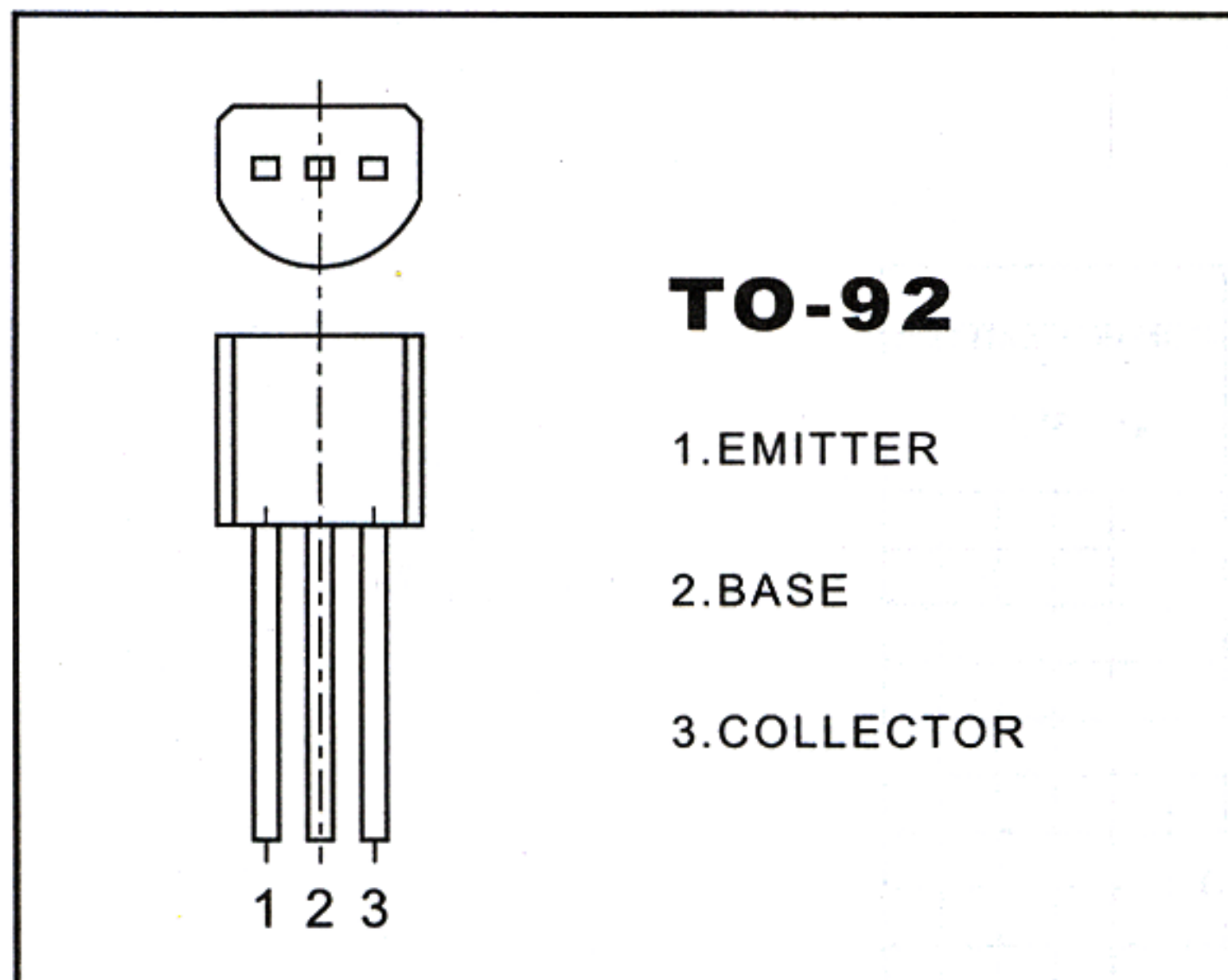


## 2SC2216 TRANSISTOR(NPN)



### FEATURES

#### Power dissipation

$P_{CM}$ : 300mW ( $T_{amb}=25^{\circ}C$ )

#### Collector current

$I_{CM}$ : 50 mA

#### Collector-base voltage

$V_{(BR)CBO}$ : 50 V

#### Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

### ELECTRICAL CHARACTERISTICS

( $T_{amb}=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	50		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10 mA, I_B = 0$	45		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	4		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 50 V, I_E = 0$		0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 4 V, I_C = 0$		0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = 12.5 V, I_C = 12.5 mA$	40	140	
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = 15 mA, I_B = 1.5 mA$		0.2	V
Base-emitter saturation voltage	$V_{BEsat}$	$I_C = 15 mA, I_B = 1.5 mA$		1.5	V
Transition frequency	$f_T$	$V_{CE} = 12.5 V, I_C = 12.5 mA$ $f = 100 MHz$	300		MHz



